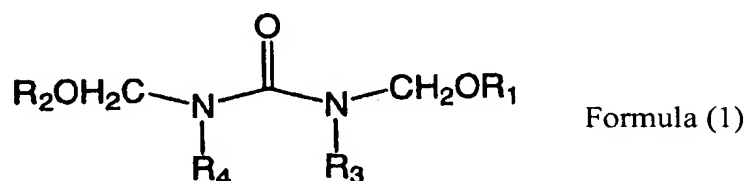


Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) ~~An composition for forming anti-reflective coating~~
forming composition, used for lithography process for manufacturing a semiconductor device
~~characterized by containing~~comprising a compound of formula (1), a condensation product
 thereof or a resin produced from the compound



wherein R₁ and R₂ are independently of each other hydrogen atom or an alkyl group, R₃ and R₄ are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxymethyl group, and an acid and/or acid generator, and the compound, the condensation product thereof or the resin produced from the compound is contained in an amount of 50 mass% or more in a solid content of the ~~composition for forming~~ anti-reflective coating forming composition.

2-3. (Canceled)

4. (Currently Amended) ~~The composition for forming anti-reflective coating~~
forming composition according to claim 1, further containing a light absorbing compound
 and/or a light absorbing resin.

5. (Currently Amended) ~~The composition for forming anti-reflective coating~~
forming composition according to claim 4, wherein the light absorbing compound is at least
 one compound selected from naphthalene compounds and anthracene compounds.

6. (Currently Amended) The ~~composition for forming anti-reflective coating~~ forming composition according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.

7. (Currently Amended) The ~~composition for forming anti-reflective coating~~ forming composition according to claim 4, wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.

8. (Currently Amended) The ~~composition for forming anti-reflective coating~~ forming composition according to claim 1, further containing a resin having at least one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.

9. (Canceled)

10. (Currently Amended) A method of forming an anti-reflective coating for use in lithography process in a manufacture of a semiconductor device, characterized by comprising the steps of: coating the ~~composition for forming anti-reflective coating~~ forming composition according to claim 1 on a substrate, and baking it.

11. (Currently Amended) A process for manufacturing a semiconductor device, characterized by comprising the steps of:

coating the ~~composition for forming anti-reflective coating~~ forming composition according to claim 1 on a substrate and baking it to form an anti-reflective coating;

forming a photoresist on the anti-reflective coating;

exposing the substrate covered with the anti-reflective coating and the photoresist with a light;

developing it;

transferring an image on the substrate by etching to form an integrated circuit

device.